1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in an enhanced LFPAK56E package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
 - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
 - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
 - Improved SOA and avalanche capability compared to standard TrenchMOS
 - Tight V_{GS(th)} limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
 - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
 - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
 - · Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
 - Improved reliability, with reduced R_{th} and R_{DSon}
 - Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- · Start-Stop micro-hybrid applications
- · Transmission control
- · Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	40	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	220	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	500	W
Static characte	Static characteristics						
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 25 °C; Fig. 11		0.6	0.85	1	mΩ



Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Dynamic chara	Oynamic characteristics							
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ Fig. 13; Fig. 14		-	17.7	35.5	nC	
Source-drain d	liode							
Q _r	recovered charge	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V		-	53.2	-	nC	
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C		-	0.77	-		

^{[1] 220}A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	r ioool i	
2	S	source	(,,-,,,-,,,)	
3	S	source		D
4	G	gate		
mb	D	mounting base; connected to drain	1 2 3 4 LFPAK56E; Power- SO8 (SOT1023)	mbb076 S

6. Ordering information

Table 3. Ordering information

Type number	number Package				
	Name	Description	Version		
BUK7J1R0-40H	1	plastic, single-ended surface-mounted package (LFPAK56E); 4 leads; 1.27 mm pitch	SOT1023		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7J1R0-40H	71H040E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25 °C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	40	V
V_{GS}	gate-source voltage		[1]	-20	20	V

Symbol	Parameter	Conditions		Min	Max	Unit
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	500	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[2]	-	220	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>	[2]	-	220	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 \text{ °C}$; Fig. 3		-	600	Α
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drain	n diode		·			
I _S	source current	T _{mb} = 25 °C	[3]	-	165	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$		-	600	Α
Avalanche ru	uggedness		·			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 190 A; $V_{sup} \le 40$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[4] [5]	-	242	mJ

- [1] Refer to application note AN90001 for further information.
- [2] 220A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [3] 165A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
- [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [5] Refer to application note AN10273 for further information.

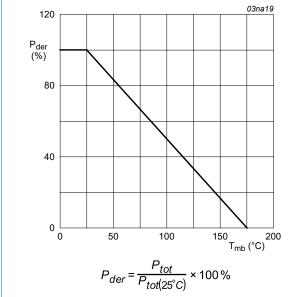
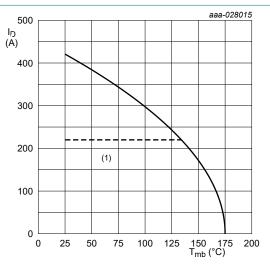


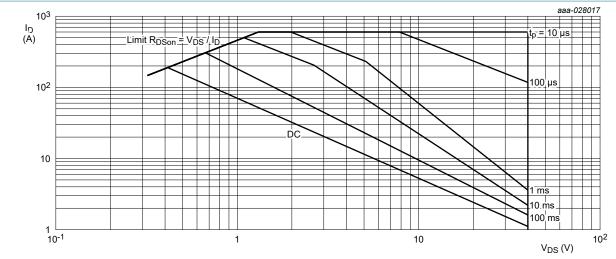
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$ (1) 220A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

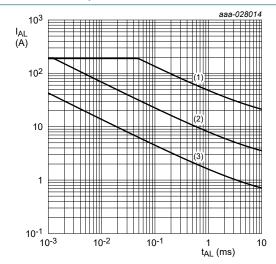
Fig. 2. Continuous drain current as a function of mounting base temperature

N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK56E



 T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j \text{ (init)}}$ = 25 °C; (2) $T_{j \text{ (init)}}$ = 150 °C; (3) Repetitive Avalanche

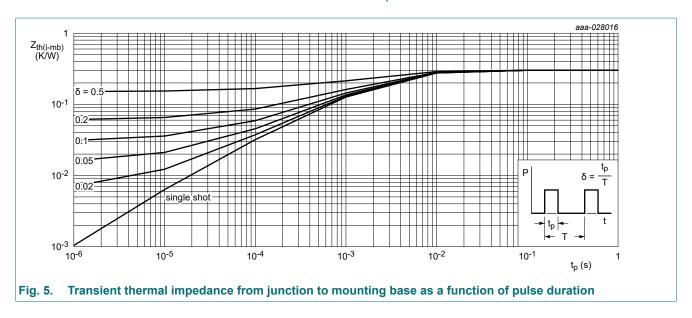
Fig. 4. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.21	0.3	K/W

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	40	43	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -40 °C	-	40.5	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	36	40	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS}=V_{GS}; T_j = 25 \text{ °C}; Fig. 9; Fig. 10}$	2.4	3	3.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}; Fig. 9$	-	-	4.3	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C; <u>Fig. 9</u>	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 40 V; V _{GS} = 0 V; T _j = 25 °C	-	0.07	1.5	μA
		V _{DS} = 16 V; V _{GS} = 0 V; T _j = 125 °C	-	3.2	25	μA
		V _{DS} = 40 V; V _{GS} = 0 V; T _j = 175 °C	-	0.34	1	mA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -16 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	0.6	0.85	1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 105 °C; Fig. 12	0.84	1.27	1.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 125 °C; Fig. 12	0.93	1.41	1.75	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 12	1.17	1.76	2.18	mΩ
R_G	gate resistance	f = 1 MHz; T _j = 25 °C	0.47	1.17	2.9	Ω
Dynamic ch	aracteristics		1	1	1	1
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 32 V; V _{GS} = 10 V;	-	90.7	131	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	25.8	40	nC
Q_{GD}	gate-drain charge	1	-	17.7	35.5	nC

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{DS} = 25 V; V _{GS} = 0 V; f = 1 MHz;	-	6666	9340	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>	-	1644	2300	pF
C _{rss}	reverse transfer capacitance		-	309	679	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	22.2	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$	-	18.9	-	ns
t _{d(off)}	turn-off delay time	1	-	51.7	-	ns
t _f	fall time		-	23.8	-	ns
Source-dra	ain diode					
V_{SD}	source-drain voltage	I _S = 25 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 16</u>	-	0.77	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	44.9	-	ns
Q _r	recovered charge	V _{DS} = 20 V	-	53.2	-	nC
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C	-	0.77	-	
		I_S = 25 A; dI_S/dt = -500 A/ μ s; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C	-	0.68	-	

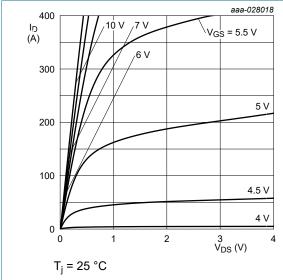


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

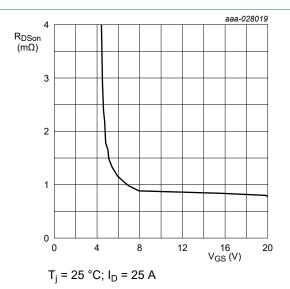


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

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N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK56E

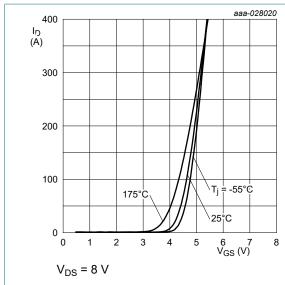


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

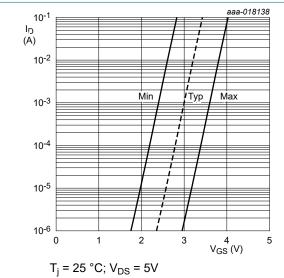


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

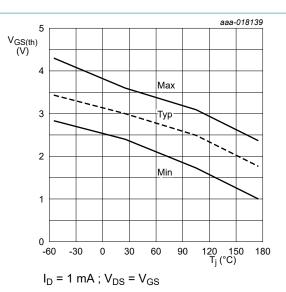


Fig. 9. Gate-source threshold voltage as a function of junction temperature

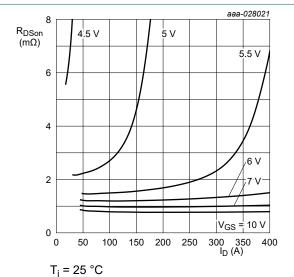


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

N-channel 40 V, 1.0 mΩ standard level MOSFET in LFPAK56E

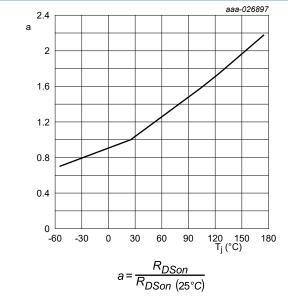


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

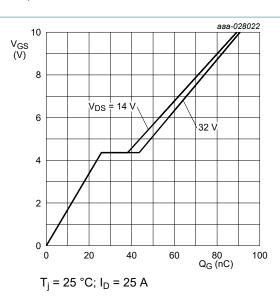


Fig. 13. Gate-source voltage as a function of gate charge; typical values

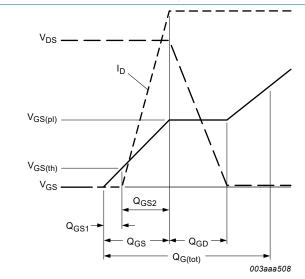


Fig. 14. Gate charge waveform definitions

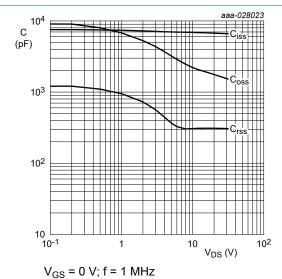
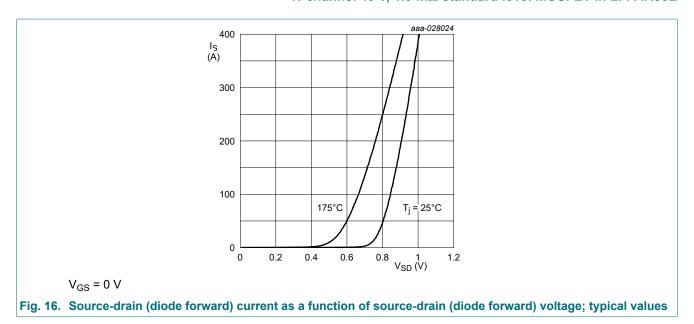


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

N-channel 40 V, 1.0 m Ω standard level MOSFET in LFPAK56E



11. Package outline

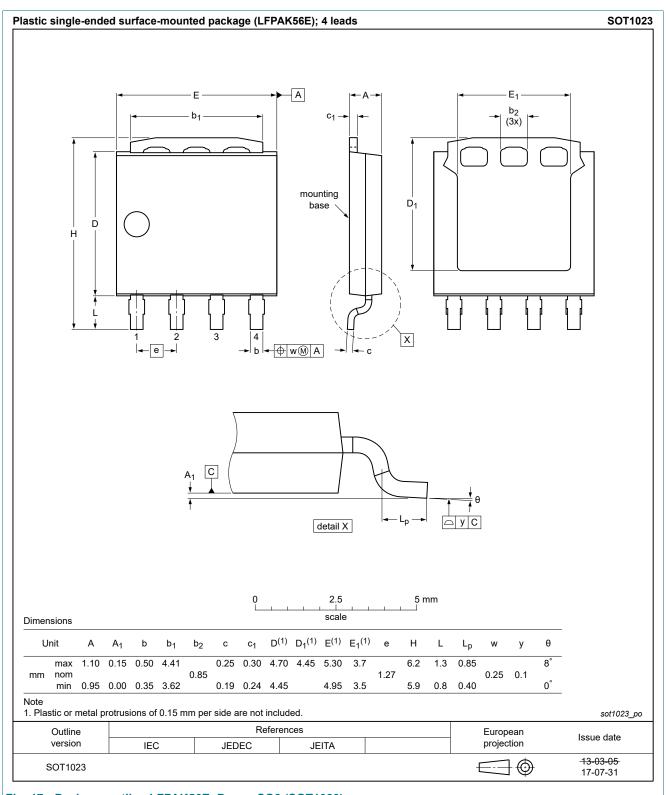


Fig. 17. Package outline LFPAK56E; Power-SO8 (SOT1023)

12. Soldering

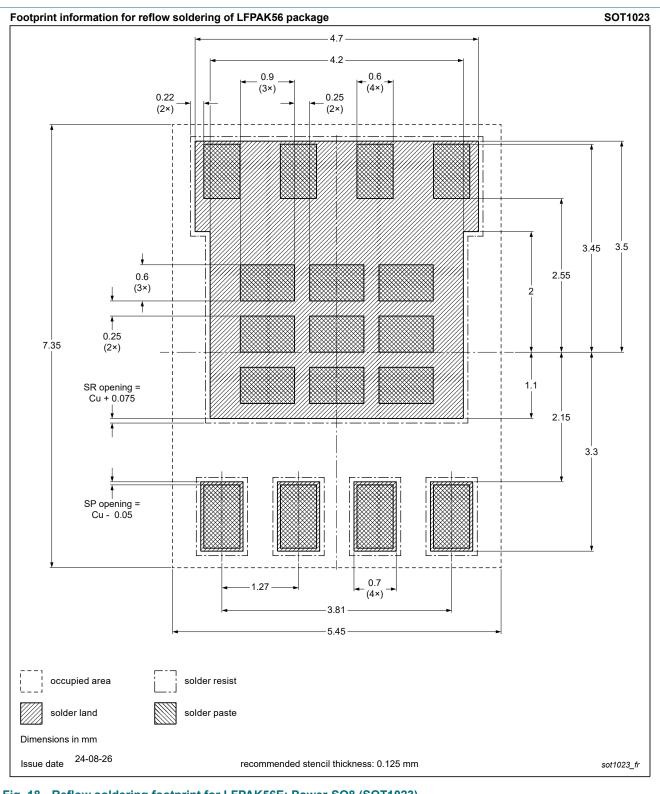


Fig. 18. Reflow soldering footprint for LFPAK56E; Power-SO8 (SOT1023)

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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Contents

1.	General description	1
2.	Features and benefits	1
3.	Applications	1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Marking	2
8.	Limiting values	2
9.	Thermal characteristics	4
10	. Characteristics	5
11.	. Package outline	10
12	. Soldering	11
	Legal information	

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